

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L2	106	((LTPS adj TFT) or (low adj temperature adj polycrystalline adj silicon adj thin adj film adj transistor))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/08 21:21
L3	10057	((438/149) or (438/151) or (438/164) or (438/166) or (438/311) or (438/412) or (438/378) or (438/479) or (438/482) or (438/486) or (438/487) or (438/488) or (438/489) or (438/490) or (438/595) or (438/596) or (438/704) or (438/406) or (438/735) or (438/745) or (438/764) or (438/795) or (438/800) or (438/902)).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/12/08 21:21
L4	103	2 and "1"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/08 21:26
L5	21	2 and 3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/08 21:22
L6	75	2 and (amorphous)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/08 22:30
L7	19	6 and 3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/08 21:26
L8	42860	(spc or (solid adj phas adj crystallization)) or (milc or (metal adj induced adj lateral adj crystallization)) or (ela or (excimer adj laser adj annealing))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/08 22:33

L9	27	8 and 2	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/08 22:33
L10	0	("2004/0217424").URPN.	USPAT	OR	OFF	2004/12/08 22:38
L11	1	("6242292").PN.	USPAT	OR	OFF	2004/12/08 22:38
L12	52	("3848104" "4046618" "4059461" "4083272" "4160263" "4234358" "4249960" "4266986" "4309225" "4328553" "4341569" "4370175" "4439245" "4463028" "4468551" "4469551" "4545823" "4734550" "4764485" "4803528" "4835704" "4862227" "4937618" "4942058" "4956539" "4970366" "5217921" "5219786" "5221365" "5247375" "5313076" "5352291" "5365875" "5372836" "5413958" "5424230" "5424244" "5432122" "5477073" "5561081" "5572046" "5578520" "5589406" "5612251" "5622814" "5648277" "5696003" "5708252" "5712191" "5736414" "5756364" "5858473").PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2004/12/08 22:40
L14	20	((("5365080") or ("5847419") or ("6607948") or ("6674100") or ("5063166") or ("4962051") or ("4962051") or ("4914053") or ("4868614")).PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/12/08 23:10
L15	2	("5818053").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/12/08 23:10
S1	10057	((438/149) or (438/151) or (438/164) or (438/166) or (438/311) or (438/412) or (438/378) or (438/479) or (438/482) or (438/486) or (438/487) or (438/488) or (438/489) or (438/490) or (438/595) or (438/596) or (438/704) or (438/406) or (438/735) or (438/745) or (438/764) or (438/795) or (438/800) or (438/902)).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/12/08 21:21

S2	12	((("4330363") or ("4592799") or ("5021119") or ("5395481") or ("6495405")).PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/12/08 23:06
S3	2901	((polycrystalline near2 silicon) or (poly adj silicon)) near2 (tft or ((thin near2 film) near2 transistor\$1))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/08 17:34
S4	1053	((polycrystalline near2 silicon) or (poly adj silicon)) near3 (spacer\$1 or sidewall\$1 or (sidewall near2 spacer\$1))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/08 21:19
S5	8	S3 and S4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/08 17:36
S6	1	S1 and S5	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/08 17:36
S7	1152	((polycrystalline near2 silicon) or (poly adj silicon)) near3 (spacer\$1 or sidewall\$1 or capp\$3 or (capp\$3 near2 (layer or film)) or (sidewall near2 spacer\$1))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/08 18:04
S8	4082	S7 and3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/08 17:39
S9	12	S7 and S3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/08 17:39

S10	1	S9 and S1	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/08 17:39
S11	11	S9 not S10	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/08 17:40
S12	16	((polycrystalline near2 silicon) or (poly adj silicon)) near3 (spacer\$1 or sidewall\$1 or (sidewall near2 spacer\$1)) same (active near2 (layer\$1 or film\$1))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/08 17:44
S13	16	((polycrystalline near2 silicon) or (poly adj silicon)) near3 (spacer\$1 or sidewall\$1 or capp\$3 or (capp\$3 near2 (layer or film)) or (sidewall near2 spacer\$1)) same (active near2 (layer\$1 or film\$1))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/08 17:54
S14	6	((polycrystalline near2 silicon) or (poly adj silicon)) near3 (spacer\$1 or sidewall\$1 or capp\$3 or (capp\$3 near2 (layer or film)) or (sidewall near2 spacer\$1)) near10 (active near2 (layer\$1 or film\$1))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/08 17:52
S15	10	S13 not S14	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/08 17:52
S16	0	("2004/0026738").URPN.	USPAT	OR	OFF	2004/12/08 17:53
S17	123	((polycrystalline near2 silicon) or (poly adj silicon)) near3 (spacer\$1 or sidewall\$1 or capp\$3 or (capp\$3 near2 (layer or film)) or (sidewall near2 spacer\$1))and (active near2 (layer\$1 or film\$1))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/08 17:55
S18	107	S17 not S13	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/08 17:55

S19	33	((polycrystalline near2 silicon) or (poly adj silicon)) near3 (spacer\$1 or sidewall\$1 or capp\$3 or (capp\$3 near2 (layer or film)) or (sidewall near2 spacer\$1)) same (crystall\$7 or recrystall\$7)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/08 18:05
S20	7	S19 and (active near2 (layer\$1 or film\$1))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/08 18:07
S21	0	S19 not S7	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/08 18:08
S22	26	S19 not S20	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/08 18:09